



RLT1550-100G

TECHNICAL DATA



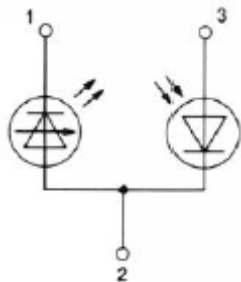
Infrared Laser Diode

Structure: **GaInAsP/InP, SQW structure**
Lasing wavelength: **typ. 1580 nm, multi mode**
Max. optical power: **100 mW**
Package: **9 mm (SOT-148)**

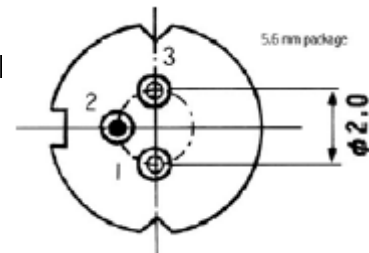
NOTE!
LASERDIODE
MUST BE COOLED!

ATTENTION
OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC SENSITIVE DEVICE

PIN CONNECTION:



- 1) Laserdiode cathode
- 2) Laserdiode anode and photodiode cathode
- 3) Photodiode anode



Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw	-	100	-	mW
Threshold Current	I _{th}	cw	300	400	600	mA
Operation Current	I _{op}	P _o = 100 mW	700	800	1000	mA
Operation Voltage	V _{op}	P _o = 100 mW	2.3	2.4	2.5	V
Lasing Wavelength	λ _p	P _o = 100 mW	-	1580	1582	nm
Spectra halfwidth (FWHM)	Δλ	P _o = 100 mW	3	4	6	nm
Beam Divergence	Θ _{//}	P _o = 100 mW	8	10	12	°
Beam Divergence	Θ	P _o = 100 mW	43	45	47	°
Emitting area	Wxd		-	100x1	-	μm x μm